

REMARKS

(1) Claims 1-18 are currently pending in the present application. Applicant cancelled Claims 19-28 herein. Applicant amended Claim 1 herein, but no new matter has been added. Applicants respectfully request reconsideration of Claims 1-18.

(2) Applicant submits that independent Claim 1 is clearly in condition for allowance, as will be discussed herein below. The accompanying remarks are necessary and were not presented earlier because Applicant did not fully understand the nature of Examiner's position. The amendments and remarks of the instant response further clarify and distinguish Applicant's invention over Examiner's grounds of rejection and supporting reasoning presented in the final office action.

(3) The Office Action cited the following reference: U. S. Patent 6,297,108 B1, by Chu, entitled *Method Of Forming A High Voltage MOS Transistor On A Semiconductor Wafer* (referred to as "Chu" hereinafter).

(4) Claims 1, 2, and 5-11 have been rejected under 35 U.S.C. § 102(b) as assertedly being anticipated by Chu. Applicant respectfully traverses these rejections for the following reasons.

Claim 1 has been amended herein to more clearly describe the invention, as recommended by the Examiner. Applicant thanks the Examiner for his input and help with making Claim 1 more clear.

Chu does not disclose, teach, suggest, or motivate forming a second doped region with a second plurality of ions within the first doped region, wherein a gate-side boundary of the second doped region is spaced away from a closest edge of the gate electrode by a first spaced distance, wherein the gate-side boundary of the second doped region is spaced away from a closest edge of the spacer by a second spaced distance, the second spaced distance being less than the first spaced distance, and wherein the spacer does not cover the second doped region, as Claim 1 requires. Because Chu does not disclose these aspects required by Claim 1, Chu cannot anticipate the invention of Claim 1.

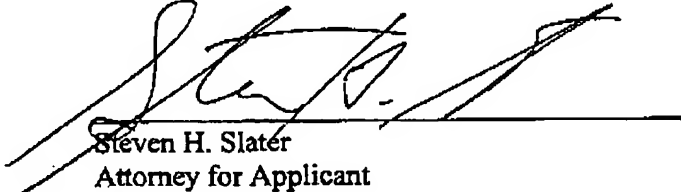
Because Claims 2-14 depend from Claim 1, Applicant respectfully submits that Claims 2-14 are patentable over Chu because of their dependency from independent claim 1 for at least the same reasons discussed above for Claim 1. Thus, Applicant respectfully asserts that Claims 1-18 are patentable over Chu, and in proper condition for allowance.

(5) Applicant thanks the Examiner for his time in considering this application. Applicant also thanks the Examiner for allowing Claims 15-18 in the prior office action.

(6) In view of the above, Applicant respectfully submits that this response complies with 37 CFR § 1.116. Applicant further submits that the claims are in condition for allowance. No new matter has been added by this amendment. If the Examiner should have any questions, please contact Applicant's attorney at the number listed below. No fee is believed to be due at this time. In the event that there are any fees due herein to keep the application pending, other than an issue fee, please charge the same, or credit any overpayment, to Deposit Account No. 50-1065.

Respectfully submitted,

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Date

  
Steven H. Slater  
Attorney for Applicant  
Reg. No. 35,361

SLATER & MATSIL, L.L.P.  
17950 Preston Rd., Suite 1000  
Dallas, Texas 75252-5793  
Tel. 972-732-1001  
Fax: 972-732-9218